

IN THE CLAIMS:

Please amend claims 1, 2, 9, 11 and 12 as follows:

1. (Amended) A semiconductor device comprising:
a base substrate;
a first conducting film formed [on] over the base substrate and including two conductor patterns adjacent to each other;
an etching stopper film covering [an] each upper surface of the [first conducting film] two conductor patterns;
a first insulation film [which is an insulation film] formed [on] over the etching stopper film and the base substrate; [and includes]
(contact)
~~a central hole, which reaches~~ located between the two conductor patterns, reaching the base substrate [between the two conductor patterns and] through the first insulation film, wherein an end of [which] the contact hole is positioned on the etching stopper film [on the conductor patterns]; and
a sidewall insulation film formed on an inner wall of the first insulation film, each side [walls] wall of the two conductor patterns [of the first conducting film], and each side wall of the etching stopper film [on the two conductor patterns] in the contact hole.

2. (Amended) A semiconductor device comprising:

a base substrate;

a first conducting film formed [on] over the base substrate and including a plurality of conductor patterns adjacent to each other;

an etching stopper film covering an upper surface of the [first conducting film] conductor patterns;

a first insulation film [which is an insulation film] selectively buried between said a plurality of conductor patterns; [and includes]

a contact hole [which reaches the base substrate] located between the adjacent conductor patterns and having an end thereof defined by the conductor patterns; and

a sidewall insulation film formed on an inner wall of the contact hole so that side walls of [the first conducting film and of] the conductor pattern and the etching stopper film [in the contact hole] are covered.

9. (Amended) A semiconductor device comprising;
a semiconductor substrate;
a plurality of word lines formed [on] over the semiconductor substrate and extended in a first direction;

an etching stopper film covering upper surfaces of the word lines;
a first insulation film [which is an insulation film] formed [on] over the etching stopper film and the semiconductor substrate; [and includes]

a contact hole, [which reaches] located between the word lines, reaching the semiconductor substrate [between the word lines] through the first insulation film, wherein [and

having] an end of [which] the contact hole is positioned on the etching stopper film [on the word lines]; and

a sidewall insulation film, formed [on] in the contact hole, covering a side wall of the first insulation film, side walls of the word lines and side walls of the etching stopper film [in the contact hole].

11. (Amended) A semiconductor device comprising:

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a semiconductor substrate;

a plurality of word lines formed [on] over the semiconductor substrate and extended in a first direction;

a first insulation film formed [on] over the word lines and the semiconductor substrate;

a plurality of bit lines formed [on] over the first insulation film and extended in a second direction which intersects the first direction;

an etching stopper film covering upper surfaces of the bit lines;

a second insulation film [which is an insulation film] formed [on] over the etching stopper film and the first insulation film; [, and includes]

a contact hole, [formed] located between the adjacent bit lines, [and] having an end thereof positioned on the etching stopper film [on the bit lines];

a sidewall insulation film, formed [on] in the contact hole, covering a side wall of the second insulation film, side walls of the bit lines and side walls of the etching stopper film [in the contact hole]; and

a capacitor having one electrode connected to the semiconductor substrate through the contact hole.

12. (Amended) A semiconductor device comprising:

a semiconductor substrate;

a plurality of word line formed [on] over the semiconductor substrate and extended in a first direction;

a first insulation film formed [on] over the word lines and the semiconductor substrate;

a plurality of bit lines formed [on] over the first insulation first and extended in a second direction which intersects the first direction;

an etching stopper film covering upper surfaces of the bit lines;

a second insulation film [which is an insulation film] selectively buried between said a plurality of bit lines; [, and includes]

a contact hole, [formed] located between the adjacent bit lines, [and] having an end thereof defined by the bit lines;

a sidewall insulation film, formed [on] in the contact hole, covering a side wall of the second insulation film, side walls of the bit lines and side walls of the etching stopper film [in the contact hole]; and

a capacitor having one electrode connected to the semiconductor substrate through the contact hole.